

2811

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PTO/SB/21 (08-00)

<b>TRANSMITTAL FORM</b>  (to be used for all correspondence after initial filing)	Application Number	09/535,015
	Filing Date	March 24, 2000
	First Named Inventor	Shunpei YAMAZAKI et al.
	Group Art Unit	2811
	Examiner Name	S. Crane
Total Number of Pages in This Submission	Attorney Docket Number	0756-2131

**ENCLOSURES (check all that apply)**

<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/ Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Declaration and Power of Attorney <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s) _____	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences <input type="checkbox"/> Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) <input type="checkbox"/> Proprietary Information <input type="checkbox"/> Status Letter <input checked="" type="checkbox"/> Other Enclosures 1. Correction to Previously Submitted Information Disclosure with PTO 1449 Form 2. 2. 3. 4. 5. 6.
<b>Remarks</b> <input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 50-2280 for the above identified docket number.		

**SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT**

Firm or Individual name	Eric J. Robinson, Reg. No. 38,285 Robinson Intellectual Property Law Office, P.C. PMB 955 21010 Southbank Street Potomac Falls, VA 20165
Signature	
Date	August 3, 2006

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Attorney Docket No. 0756-2131

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re Patent Application of:

Shunpei YAMAZAKI et al.

Serial No. 09/535,015

Filed: March 24, 2000

For: METHOD OF MANUFACTURING A  
SEMICONDUCTOR DEVICE

) Group Art Unit: 2811

) Examiner: S. Crane

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) 2006.

*Adam M. Stamps*

**INFORMATION DISCLOSURE STATEMENT AND CORRECTION OF PREVIOUSLY  
SUBMITTED INFORMATION DISCLOSURE STATEMENT**

Honorable Commissioner of Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

It has come to applicant's attention that several Information Disclosure Statements previously submitted included inadvertent typographical errors or incomplete information.

Specifically, the Information Disclosure Statement filed December 19, 2000 included the following inaccuracies:

1) EP 0 178 447 was incorrectly listed with a publication date of 09/10/1984.

The correct publication date is 04/23/1986; and

2) Several articles did not include an appropriate title, page number, spelling of the author's name, or publication.

The Information Disclosure Statements filed September 5, 2001 and March 17, 2003 included articles which did not include a publication date and page number.

The above inaccuracies are corrected on the 1449 Form attached hereto. The Examiner is requested to initial the attached PTO Form 1449 evidencing consideration of the above references and line through these references on the previously submitted

Information Disclosure Statements to ensure that the correct information is printed correctly on any issued patent.

Respectfully submitted,



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Eric J. Robinson  
Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C.  
PMB 955  
21010 Southbank Street  
Potomac Falls, Virginia 20165  
(571) 434-6789

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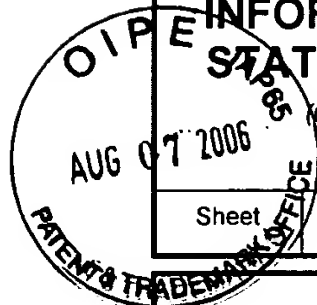
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Substitute for form 1449A/PTO			<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)			Application Number	09/535,015
			Filing Date	March 24, 2000
			First Named Inventor	Shunpei YAMAZAKI et al.
			Group Art Unit	2811
			Examiner Name	Sara W. Crane
Sheet 1	of	2	Attorney Docket Number	0756-2131



FOREIGN PATENT DOCUMENTS								
Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
		EP	0 178 447			04/23/1986		Eng.

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		STOEMENOS et al., <i>Crystallization of Amorphous Silicon by Reconstructive Transformation Utilizing Gold</i> , Appl. Phys. Lett., Volume 58, No. 11, March 18, 1991, Pages 1196-1198.	
		KUZNETSOV et al., <i>Enhanced Solid Phase Epitaxial Recrystallization of Amorphous Silicon Due to Nickel Silicide Precipitation Resulting from Ion Implantation and Annealing</i> , Nuclear Instruments and Methods in Physics Research, 880/881, 1993, Pages 990-993.	
		HATALIS et al., <i>High Performance Thin-Film Transistors in Low Temperature Crystallized LPCVD Amorphous Silicon Films</i> , IEEE Electron Device Letters, Vol. EDL 8, No. 8, August 1987, Pages 361-364.	
		LAU et al., <i>Solid Phase Epitaxy Silicide-Forming Systems</i> , Thin Solid Films, Volume 47, No. 3, 1977, Pages 313-322.	
		KAWAZU et al., <i>Initial Stage of the Interfacial Reaction Between Nickel and Hydrogenated Amorphous Silicon</i> , Japanese Journal of Applied Physics, Volume, 29, No. 4, April 1, 1990, Pages 729-738.	
		HEMPEL et al., <i>Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films</i> , Solid State Communications, Volume 85, No. 11, 1993, Pages 921-924.	
		KUO, <i>PD Introduced Lateral Crystallization of Amorphous Silicon Thin Films at Low Temperature</i> , Thin Film Transistor Technologies, Volume 94-35, Pages 116-122.	
		WOLF et al., <i>Silicon Processing for the VLSI Era</i> , Volume 1: Process Technology, Lattice Press, 1986, Pages 207-211.	
		DVURECHENSKII et al., <i>Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals</i> , Phys. Stat. Sol. (a), Volume 95, No. 635, 1986, Pages 635-640.	

Examiner Signature	Date Considered
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Substitute for form 1449A/PTO

**Complete if Known**

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Group Art Unit	2811
Examiner Name	Sara W. Crane
Attorney Docket Number	0756-2131

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Sheet 2 of 2

**FOREIGN PATENT DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				

**OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		HAYZELDEN et al., <i>Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films</i> , J. Appl. Phys., Volume 73, No. 12, June 15, 1993, Pages 8279-8289.	
		KUZNETSOV et al., <i>Silicide Precipitate Formation and Solid Phase Re-Growth of Ni<sup>+</sup>-Implanted Amorphous Silicon</i> , Inst. Phys. Conf. Ser. No. 134.4: Proceedings of the Royal Microscopical Society Conf., April 5-8, 1993, Pages 191-194.	
		BAKER, JR. et al., <i>Field Effect Transistor</i> , IBM Technical Disclosure Bulletin, Volume 11, No. 7, December 1968, Page 849.	
		WOLF, <i>Silicon Processing for the VLSI Era</i> , Volume 2: Process Integration, 1990, Pages 273-274.	
		CAUNE et al., <i>Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact with Some Metals</i> , Applied Surface Science, Volume 36, January 1, 1989, Pages 597-604.	

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